

Q1 towards the central portion of the channel region and decreases toward the opposing source and drain regions.

Q2 9. (amended) A transistor comprising, in a well structure of a substrate, a source and a drain region and a channel region separating the source and the drain region, said channel region having a non-uniform concentration of dopant, wherein said non-uniform concentration comprises a retrograde concentration distribution in the direction away from the surface of the substrate, and wherein said non-uniform concentration comprises a lateral concentration distribution along the length of the channel that is higher in a region generally towards the central portion of the channel region and decreases toward the opposing source and drain regions.

Kindly cancel claims 1 - 2, and 10 - 11.

Please enter the following new claims:

Q3 Sub E' --13. (new) The transistor of claim 9, wherein the transistor is an NMOS transistor.

14. (new) The NMOS transistor of claim 13, wherein the NMOS transistor is a floating gate transistor.--

A marked-up version of the amended claims is attached as Exhibit A

IN THE SPECIFICATION

Please replace the paragraph beginning on page 5, line 4 with the following paragraph:

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